Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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MC74HCT138A

1-of-8 Decoder/ Demultiplexer with LSTTL Compatible Inputs

High−Performance Silicon−Gate CMOS

The MC74HCT138A is identical in pinout to the LS138. The HCT138A may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

The HCT138A decodes a three−bit Address to one−of−eight active−lot outputs. This device features three Chip Select inputs, two active−low and one active−high to facilitate the demultiplexing, cascading, and chip−selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- Pb−Free Packages are Available*

ON Semiconductor®

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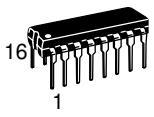
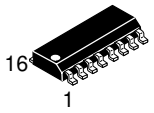
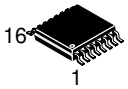
MARKING DIAGRAMS



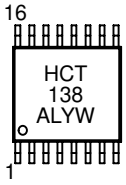
PDIP−16
N SUFFIX
CASE 648



SOIC−16
D SUFFIX
CASE 751B



TSSOP−16
DT SUFFIX
CASE 948F



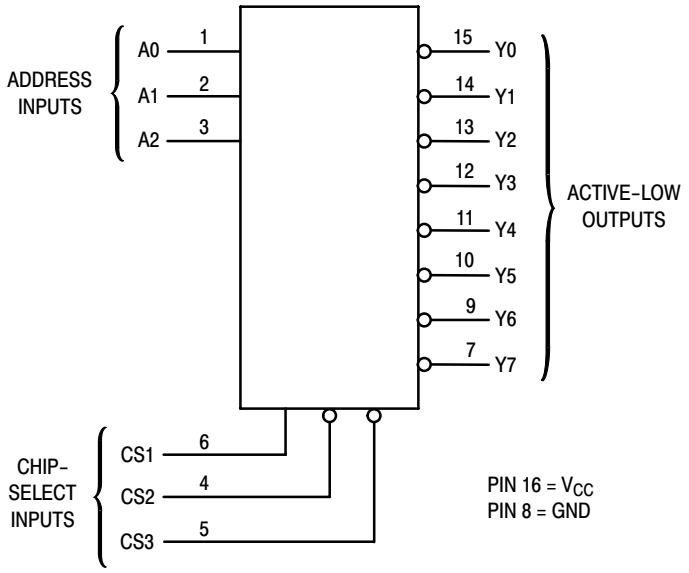
A	=	Assembly Location
WL, L	=	Wafer Lot
Y, YY	=	Year
W, WW	=	Work Week
G	=	Pb−Free Package

ORDERING INFORMATION

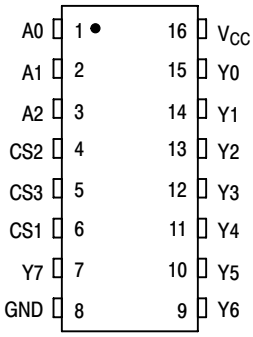
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

LOGIC DIAGRAM



PIN ASSIGNMENT



Design Criteria	Value	Units
Internal Gate Count*	30.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	pJ

*Equivalent to a two–input NAND gate.

FUNCTION TABLE

Inputs						Outputs							
CS1	CS2	CS3	A2	A1	A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

H = high level (steady state)
L = low level (steady state)
X = don't care

ORDERING INFORMATION

Device	Package	Shipping†
MC74HCT138AN	PDIP–16	500 Units / Box
MC74HCT138ANG	PDIP–16 (Pb–Free)	500 Units / Box
MC74HCT138AD	SOIC–16	48 Units / Rail
MC74HCT138ADG	SOIC–16 (Pb–Free)	48 Units / Rail
MC74HCT138ADR2	SOIC–16	2500 Units / Tape & Reel
MC74HCT138ADR2G	SOIC–16 (Pb–Free)	2500 Units / Tape & Reel
MC74HCT138ADTR2	TSSOP–16*	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, TSSOP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C
SOIC Package: – 7 mW/°C from 65° to 125°C
TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				– 55 to 25°C	≤ 85°C	≤ 125°C	
V_{IH}	Minimum High–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V_{OH}	Minimum High–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 4.0 μA	4.5	3.98	3.84	3.7	
V_{OL}	Maximum Low–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 4.0 mA	4.5	0.26	0.33	0.4	
I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in} = V_{CC} or GND I_{out} = 0 μA	5.5	4.0	40	160	μA
		V_{in} = 2.4 V, Any One Input		≥ – 55°C	25°C to 125°C		
ΔI_{CC}	Additional Quiescent Supply Current	V_{in} = V_{CC} or GND, Other Inputs I_{out} = 0 μA	5.5	2.9	2.4		mA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 V ± 10%, C_L = 50 pF, Input $t_r = t_f$ = 6.0 ns)

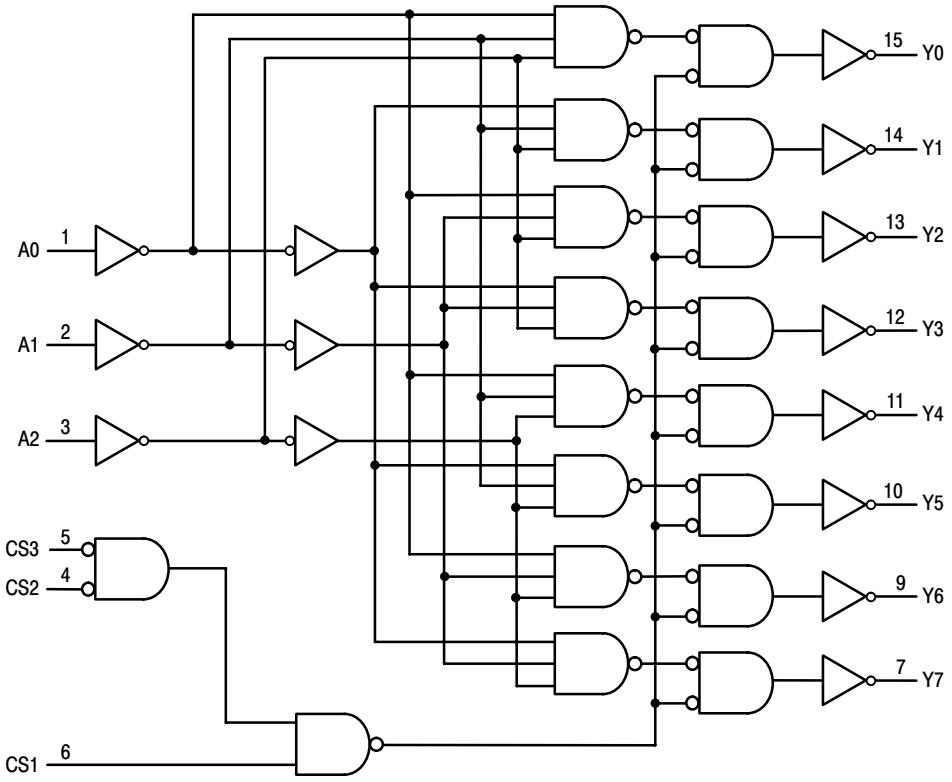
Symbol	Parameter	Guaranteed Limit			Unit
		– 55 to 25°C	≤ 85°C	≤ 125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4)	30	38	45	ns
t_{PLH}, t_{PHL}	Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4)	27	34	41	ns
t_{PLH}, t_{PHL}	Maximum Output Transition Time, CS2 or CS3 to Output Y (Figures 3 and 4)	30	38	45	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	15	19	22	ns
t_r, t_f	Maximum Input Rise and Fall Time	500	500	500	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	51	pF

* Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

EXPANDED LOGIC DIAGRAM



SWITCHING WAVEFORMS

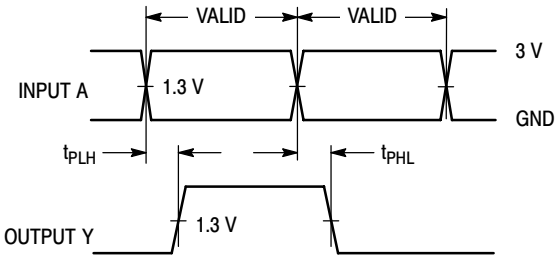


Figure 1.

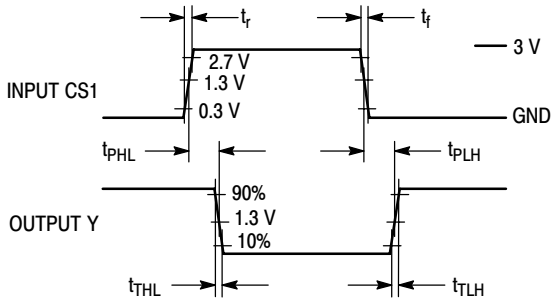


Figure 2.

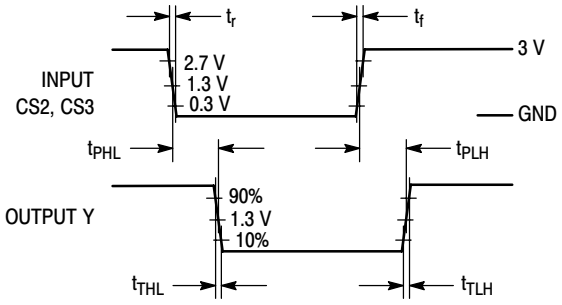
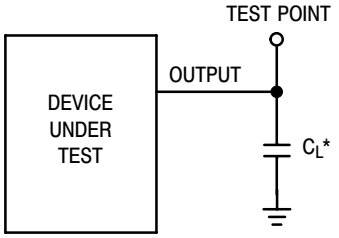


Figure 3.

TEST CIRCUIT

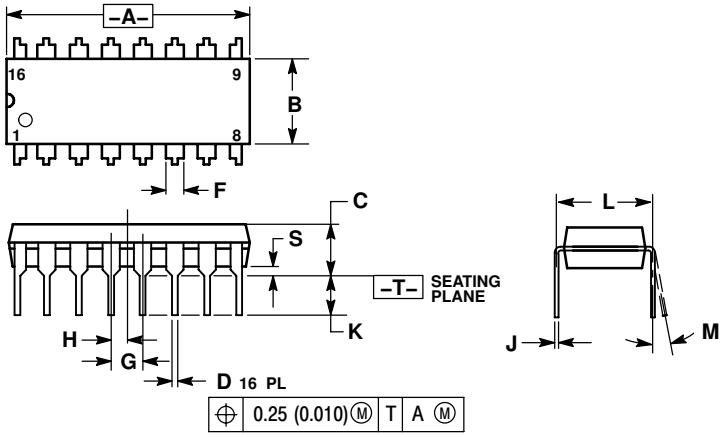


*Includes all probe and jig capacitance

Figure 4.

PACKAGE DIMENSIONS

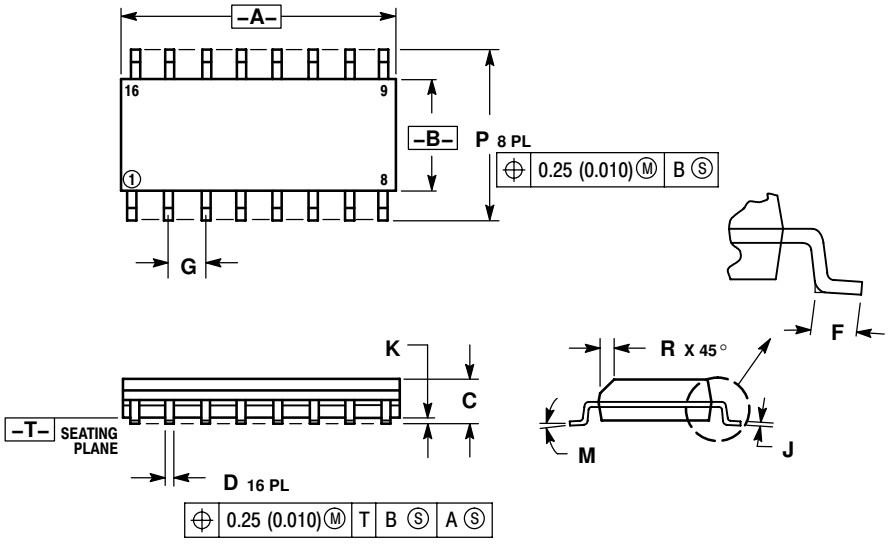
PDIP–16
N SUFFIX
CASE 648–08
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

SOIC–16
D SUFFIX
CASE 751B–05
ISSUE J

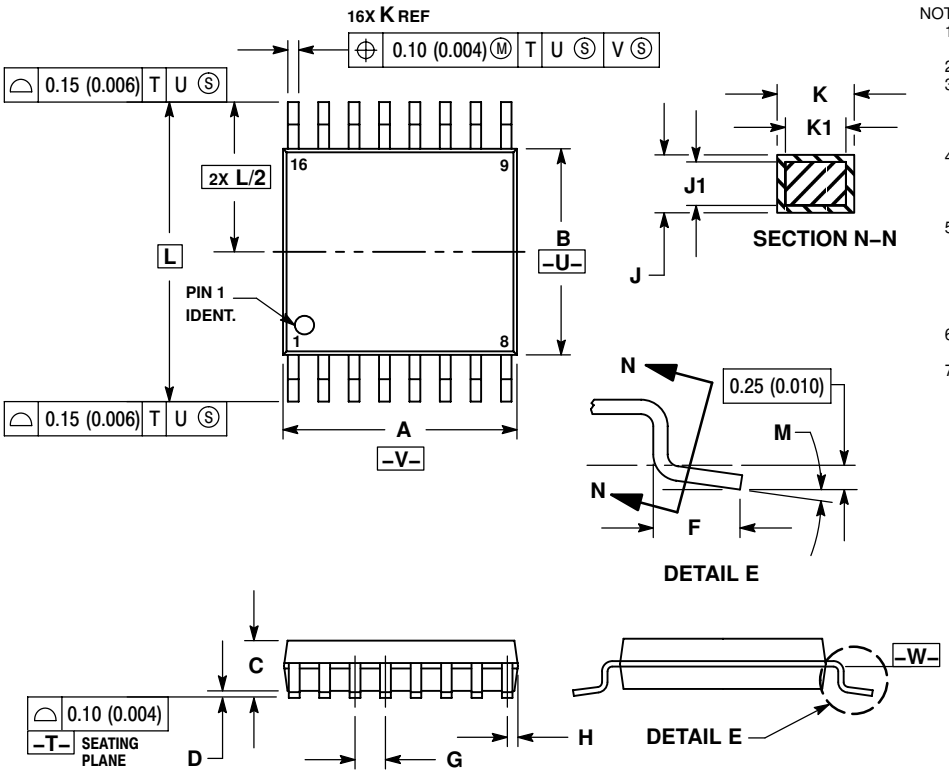


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP−16
DT SUFFIX
CASE 948F−01
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

PUBLICATION ORDERING INFORMATION

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